

LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-28 (Cancelled)

29. (Previously Presented) An in-plane switching liquid crystal display device comprising:

- a first substrate and a second substrate;
- a gate line and a common line on the first substrate;
- a first insulating layer over the gate line;
- a data line on the first insulating layer and perpendicular to the gate line;
- a thin film transistor at a crossing point of the gate and data lines; the thin film transistor including a source electrode, a drain electrode and a gate electrode;
- a second insulating layer of an organic material over the first substrate;
- transparent pixel electrodes on the second insulating layer;
- transparent common electrodes on the second insulating layer, wherein the common electrodes and the pixel electrodes form an alternating pattern, the common electrodes including an outermost common electrode adjacent to the data line;
- a capacitor electrode overlapping the common line and connected to the pixel electrodes via a contact hole, wherein the capacitor electrode and common line form a storage capacitor having the first insulating layer therebetween;
- an auxiliary pixel electrode on the second insulating layer and connected to the drain electrode through a contact hole in the second insulating layer;
- an auxiliary common electrode on the second insulating layer, wherein the auxiliary common electrode electrically contacts respective first ends of the common electrodes and

electrically contacts the common line via a contact hole through the first and second insulating layers; and

a liquid crystal layer between the first and second substrates,

wherein the outermost common electrode and the data line are on different layers and wherein a portion of the outermost common electrode overlaps the data line.

30. (Cancelled)

31. (Previously Presented) The in-plane switching liquid crystal display device of claim 29, wherein the pixel electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

32. (Cancelled)

33. (Previously Presented) The in-plane switching liquid crystal display device of claim 29, wherein the common electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

34. (Cancelled)

35. (Previously Presented) The in-plane switching liquid crystal display device of claim 29, wherein the auxiliary pixel electrode electrically contacts the pixel electrodes.

36. (Cancelled)

37. (Previously Presented) A method of fabricating an in-plane switching liquid crystal display device, comprising:

depositing and patterning a first metal on a first substrate to form a gate line and a common line on the first substrate, the gate line including a gate electrode;

forming a first insulating layer over the gate line;

forming an active layer on the first insulating layer;

depositing and patterning a second metal on the first insulating layer to form a data line perpendicular to the gate line and source and drain electrodes;

forming a second insulating layer of an organic material over the first insulating layer, the second metal and the active layer, the second insulating layer having a contact hole;

depositing and patterning a conductive material on the second insulating layer to form transparent pixel electrodes and transparent common electrodes on the second insulating layer, wherein the common electrodes include an outermost common electrode adjacent to the data line;

forming a capacitor electrode overlapping the common line and electrically connected to the pixel electrodes via a contact hole, wherein the capacitor electrode and common line form a storage capacitor having the first insulating layer therebetween;

forming an auxiliary pixel electrode on the second insulating layer and connected to the drain electrode through the contact hole;

forming an auxiliary common electrode on the second insulating layer, wherein the auxiliary common electrode electrically contacts respective first ends of the common electrodes and electrically contacts the common line via a contact hole through the first and second insulating layers; and

interposing a liquid crystal layer between the first substrate and a second substrate, wherein the outermost common electrode and the data line are on different layers and wherein a portion of the outermost common electrode overlaps the data line.

38. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the common electrodes and the pixel electrodes form an alternating pattern.

39. (Cancelled)

40. (Previously Presented) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the pixel electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

41. (Cancelled)

42. (Previously Presented) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the common electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

43. (Previously Presented) The method of fabricating an in-plane switching liquid crystal display device of claim 37, further comprising forming an auxiliary electrode on the second insulating layer, the auxiliary electrode electrically contacting one of the source and drain electrodes through a contact hole.

44. (Cancelled)

45. (Previously Presented) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the auxiliary pixel electrode electrically contacts the pixel electrodes.

46. (Cancelled)

47. (Withdrawn) An in-plane switching liquid crystal display device, comprising:

- a first substrate and a second substrate;
- a gate line and a common line on the first substrate;
- a data line perpendicular to the gate line;
- a thin film transistor including a source electrode, a drain electrode and a gate electrode;
- an insulating layer on the thin film transistor, the insulating layer having a contact hole above one of the source electrode and the drain electrode;
- a plurality of common electrodes on the insulating layer;
- a plurality of pixel electrodes on the insulating layer; and
- an auxiliary electrode contacting the one of the source electrode and the drain electrode through the contact hole.